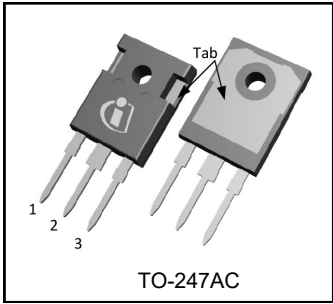
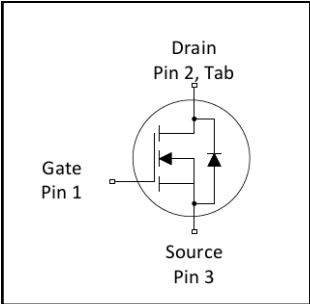


V_{DSS}	200V
$R_{DS(on)}$ typ.	17mΩ
max.	21mΩ
I_D	75A



Applications

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

Benefits

- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free, RoHS Compliant

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFP4127PbF	TO-247	Tube	25	IRFP4127PbF

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	75	A
$I_D @ T_C = 100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	53	
I_{DM}	Pulsed Drain Current ①	300	
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	341	W
	Linear Derating Factor	2.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery ③	5.7	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lbf.in (1.1N.m)	

Avalanche Characteristics

E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	244	mJ
------------------------------	---------------------------------	-----	----

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑧	—	0.4	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient ⑦⑨	—	40	

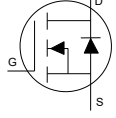
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.23	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 5mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	17	21	m Ω	$V_{GS} = 10V, I_D = 44A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 200V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
R_G	Gate Resistance	—	3.0	—	Ω	

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	45	—	—	S	$V_{DS} = 50V, I_D = 44A$
Q_g	Total Gate Charge	—	100	150	nC	$I_D = 44A$
Q_{gs}	Gate-to-Source Charge	—	30	—		$V_{DS} = 100V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	31	—		$V_{GS} = 10V$ ⑤
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	69	—		$I_D = 44A, V_{DS} = 0V, V_{GS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = 100V$
t_r	Rise Time	—	18	—		$I_D = 44A$
$t_{d(off)}$	Turn-Off Delay Time	—	56	—		$R_G = 2.7\Omega$
t_f	Fall Time	—	22	—		$V_{GS} = 10V$
C_{iss}	Input Capacitance	—	5380	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	410	—		$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	86	—		$f = 1.0\text{ MHz}$,
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)	—	360	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 160V$ ⑥
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related)	—	590	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 160V$ 10V ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode) ①	—	—	75	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	300		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 44A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	136	—	ns	$T_J = 25^\circ\text{C}$
		—	139	—		$T_J = 125^\circ\text{C}$
Q_{rr}	Reverse Recovery Charge	—	458	—	nC	$T_J = 25^\circ\text{C}$
		—	688	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	8.3	—	A	$T_J = 25^\circ\text{C}$

Notes:

- ① Repetitive rating; pulse width limited by max. Junction temperature.
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.25mH$, $R_G = 25\Omega$, $I_{AS} = 44A$, $V_{GS} = 10V$. Part not Recommended for use above this value.
- ③ $I_{SD} \leq 44A$, $di/dt \leq 760A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑤ $C_{oss \text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-0994
- ⑧ R_θ is measured at T_J approximately 90°C .

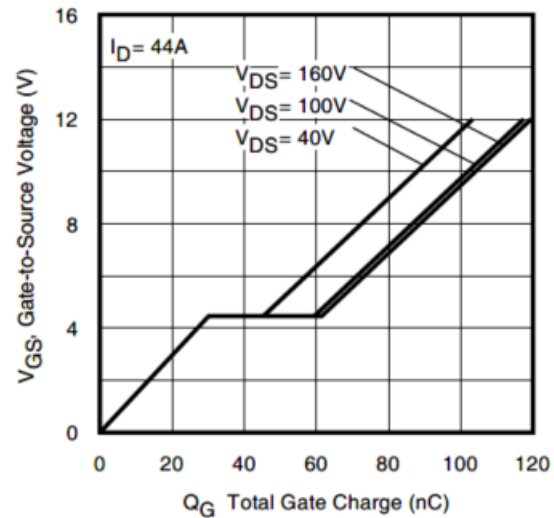
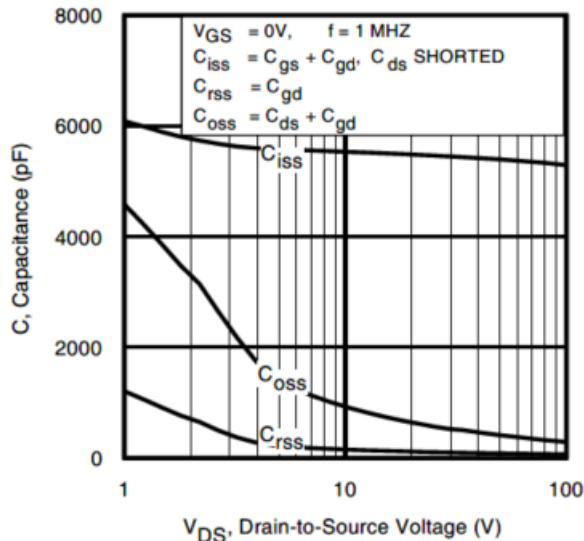
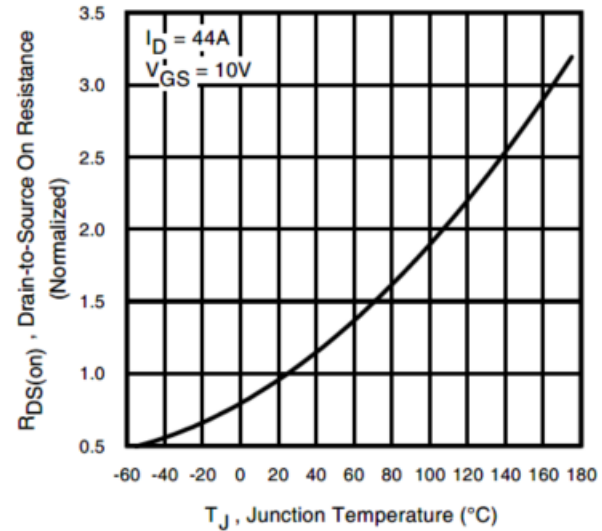
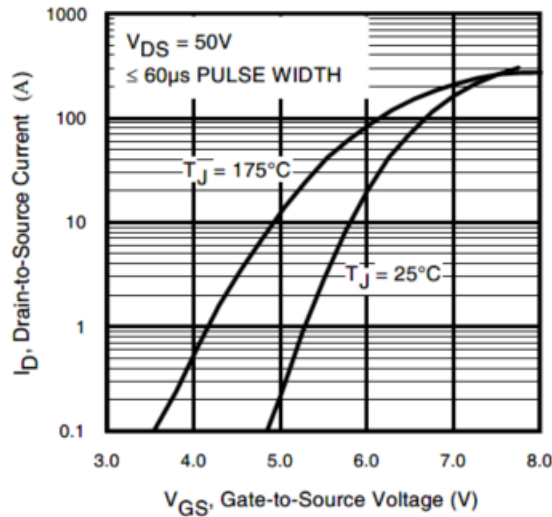
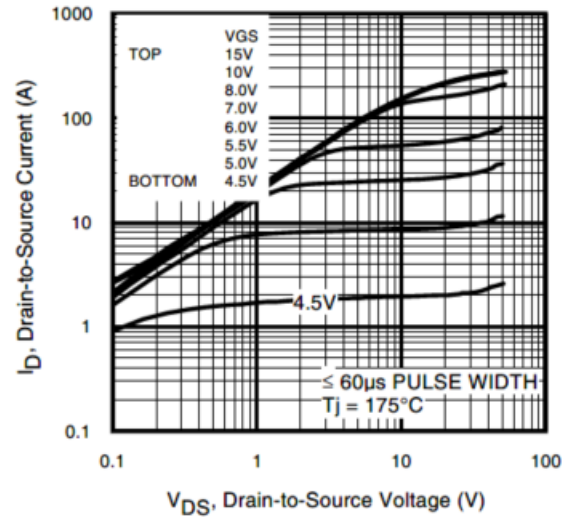
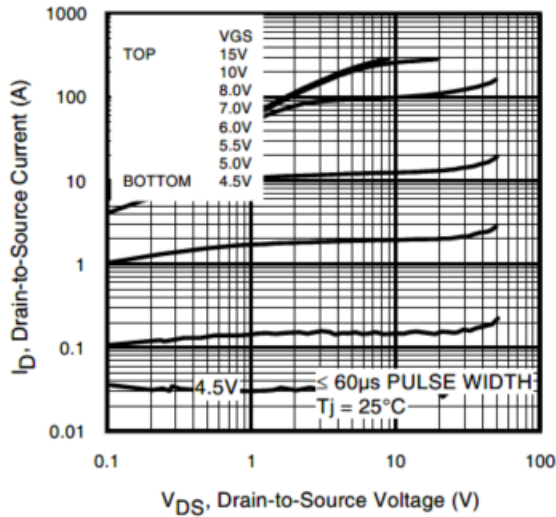


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

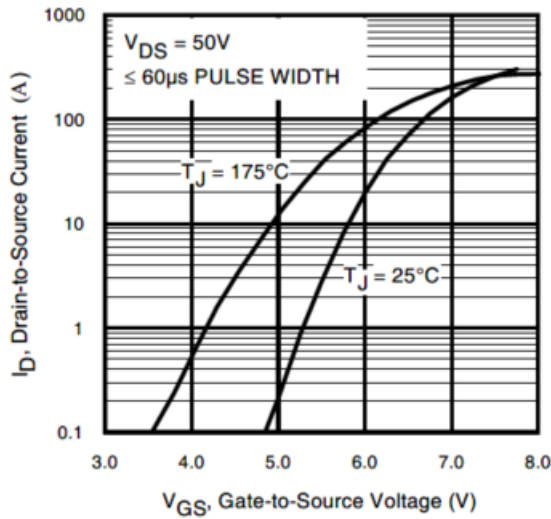


Fig 7. Typical Source-to-Drain Diode Forward Voltage

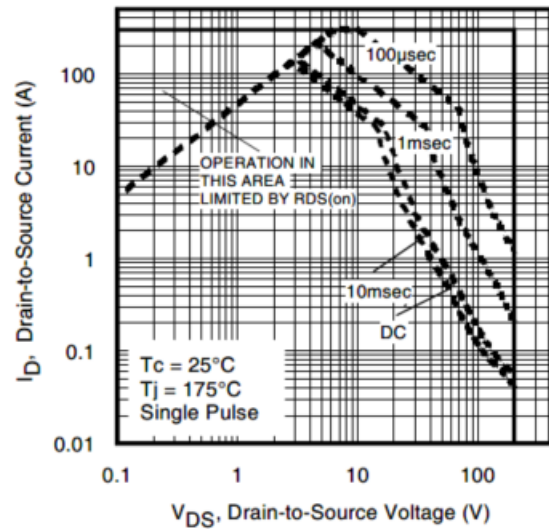


Fig 8. Maximum Safe Operating Area

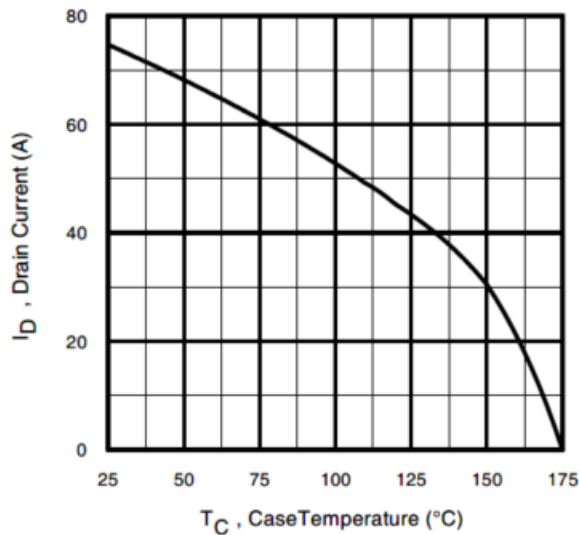


Fig 9. Maximum Drain Current vs. Case Temperature

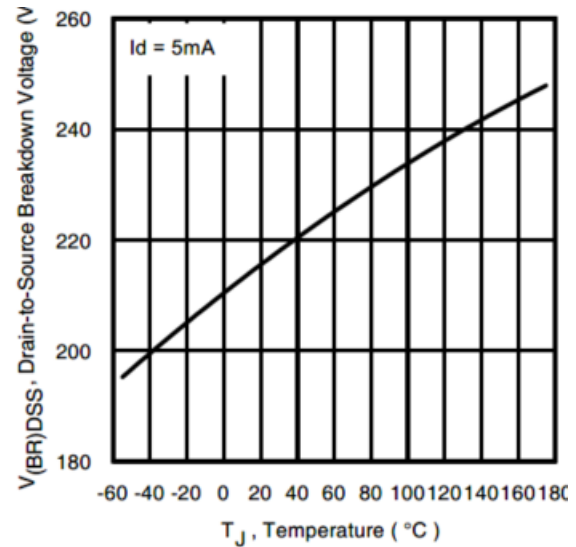


Fig 10. Drain-to-Source Breakdown Voltage

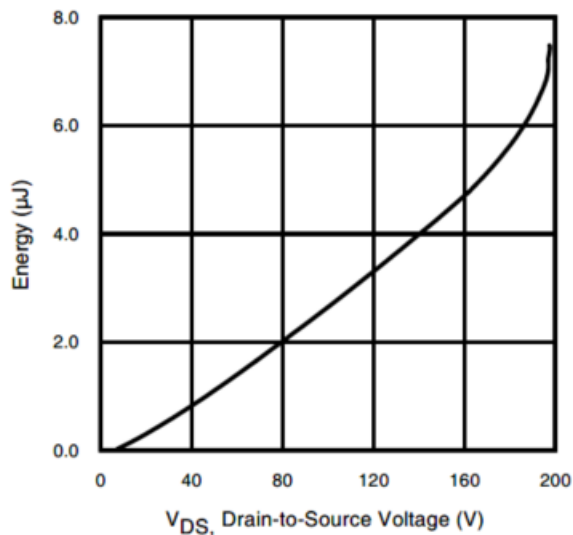


Fig 11. Typical Coss Stored Energy

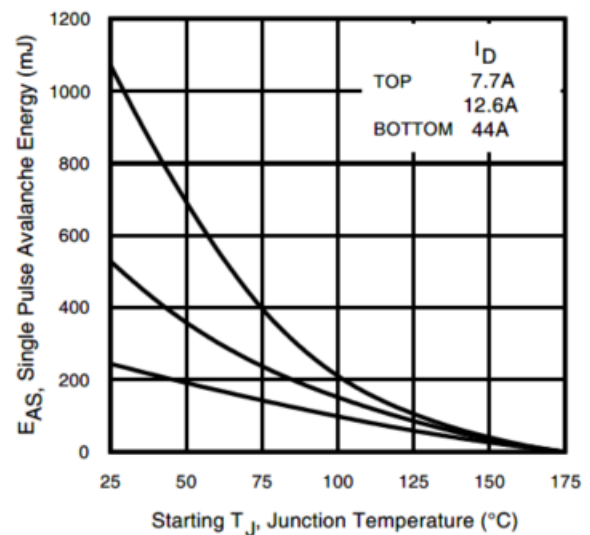


Fig 12. Maximum Avalanche Energy vs. Drain Current

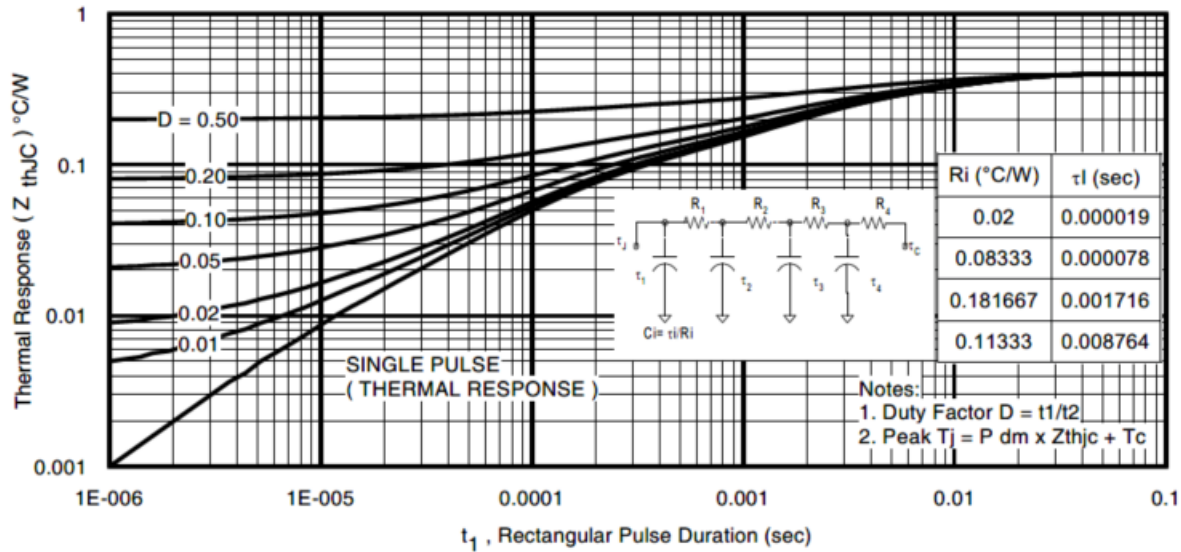


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

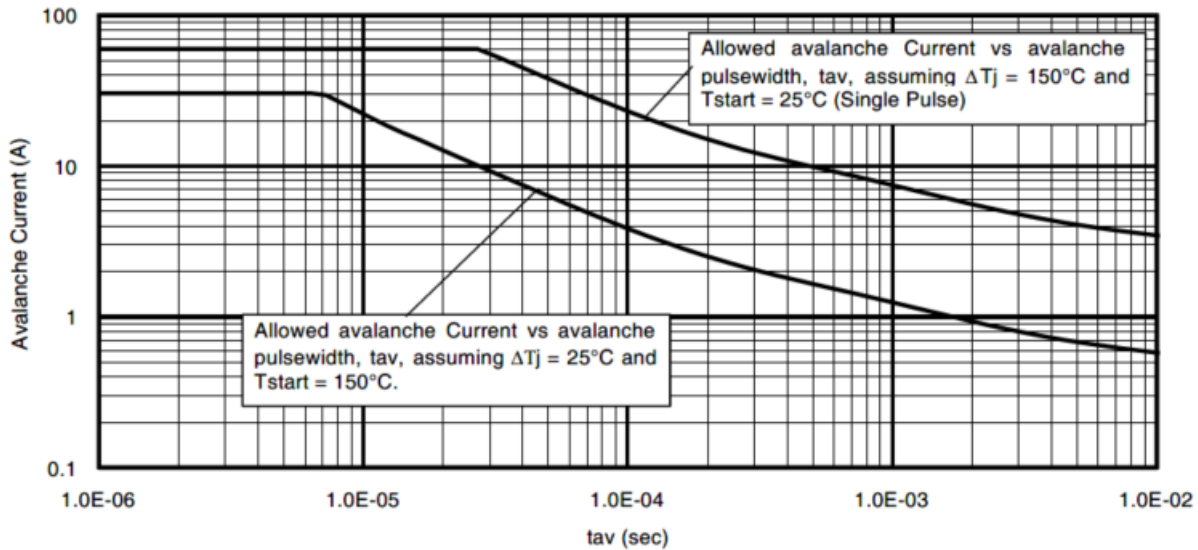
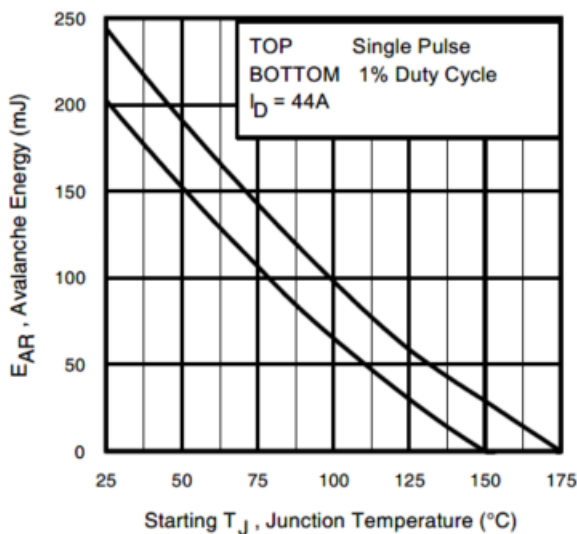


Fig 14. Typical Avalanche Current vs. Pulsewidth



Notes on Repetitive Avalanche Curves, Figures 14, 15:
 (For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{thJC}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature

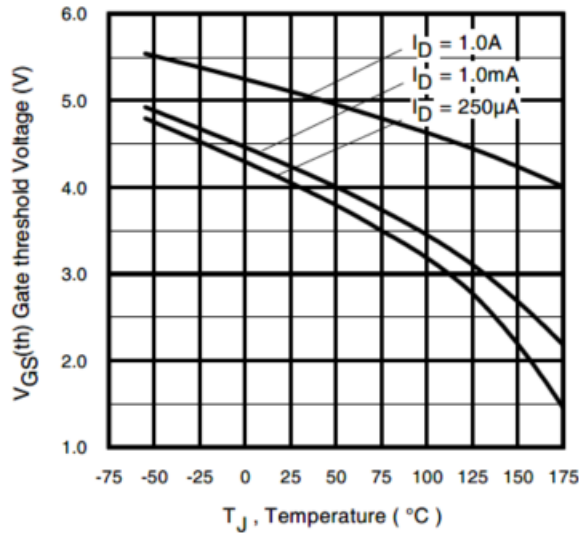
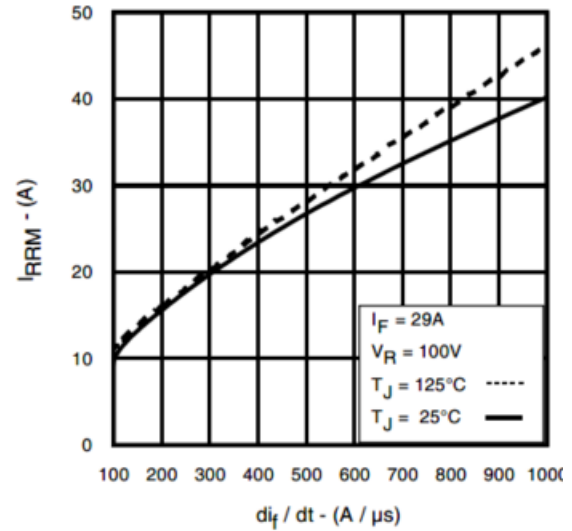
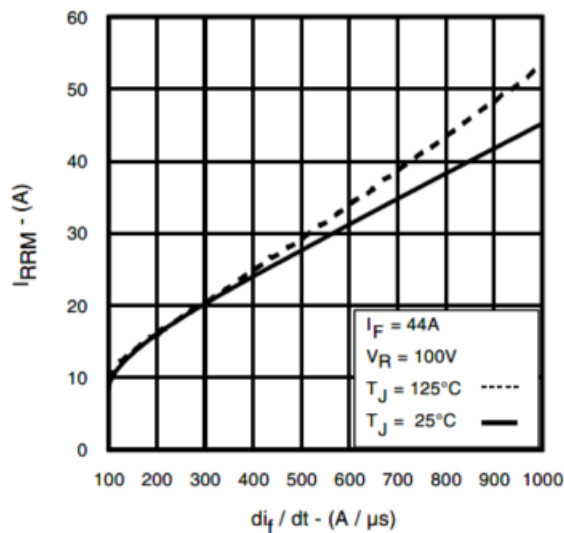
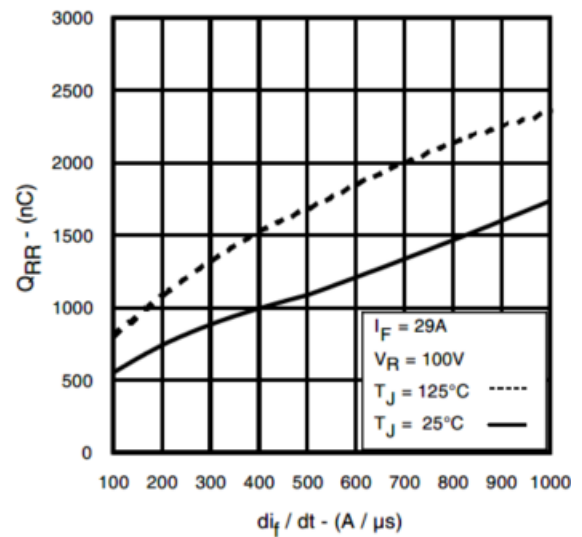
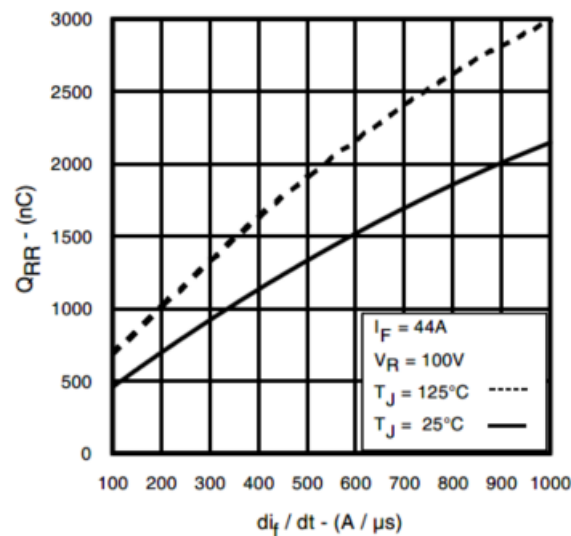


Fig. 16 Threshold Voltage vs. Temperature

Fig. 17 Typical Recovery Current vs. di_T/dt Fig 18. Typical Recovery Current vs. di_T/dt Fig 19. Typical Stored Charge vs. di_T/dt Fig 20. Typical Stored Charge vs. di_T/dt

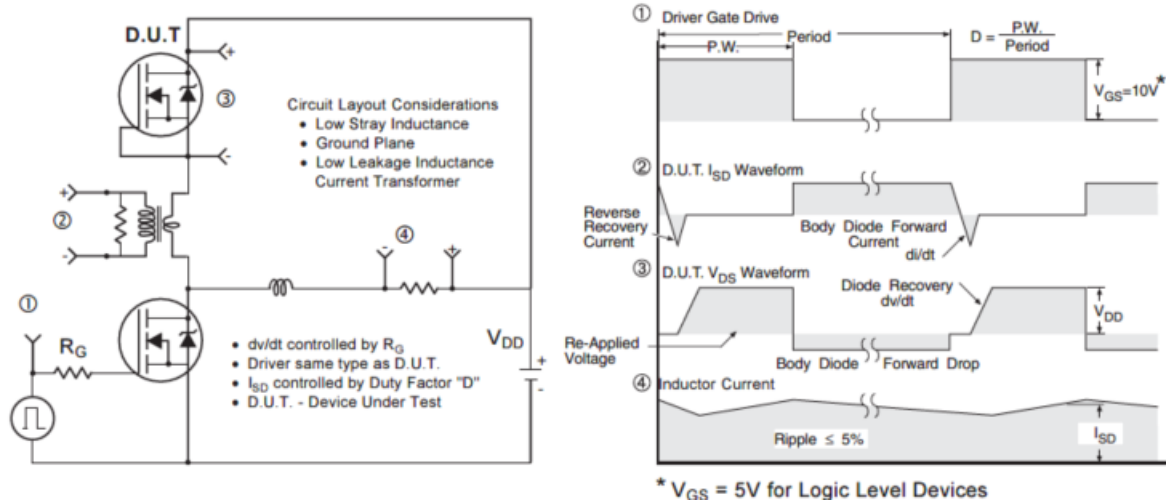


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

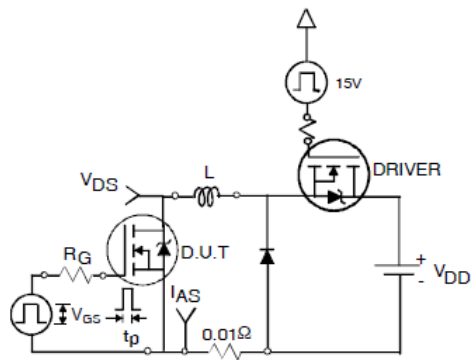


Fig 22a. Unclamped Inductive Test Circuit

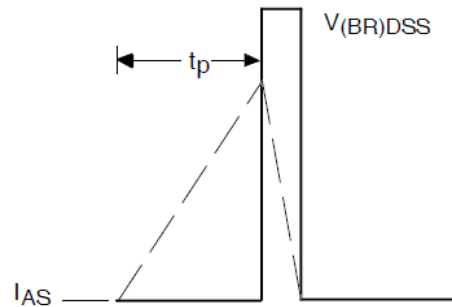


Fig 22b. Unclamped Inductive Waveforms

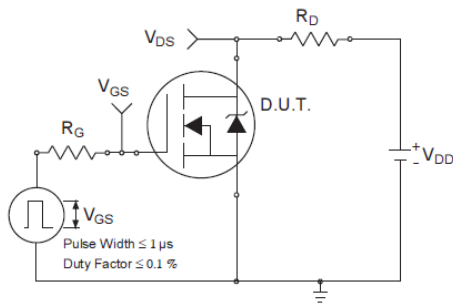


Fig 23a. Switching Time Test Circuit

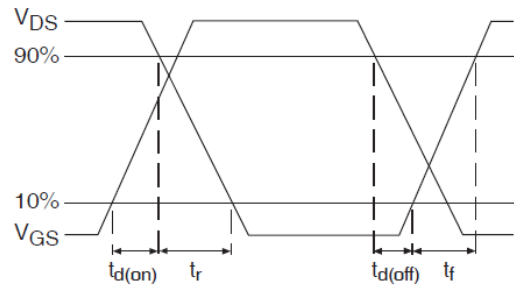


Fig 23b. Switching Time Waveforms

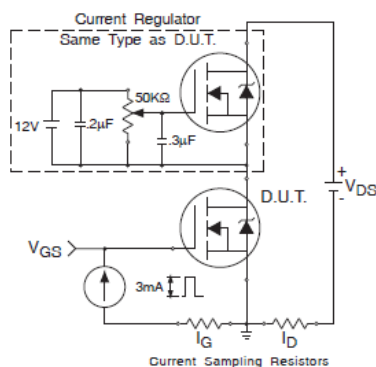


Fig 24a. Gate Charge Test Circuit

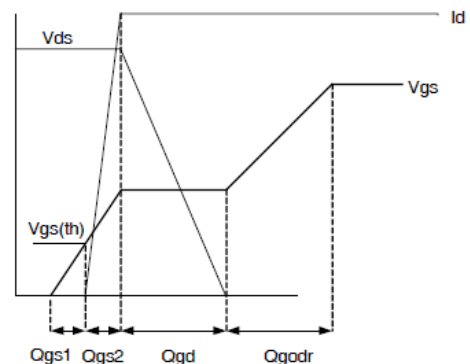


Fig 24b. Gate Charge Waveform

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.

2. DIMENSIONS ARE SHOWN IN INCHES.

3. CONTOUR OF SLOT OPTIONAL.

4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.

5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.

6. LEAD FINISH UNCONTROLLED IN L1.

7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.

8. OUTLINE CONFORMS TO JEDEC OUTLINE 20-247AC.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	1.35	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
ek	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
øP	.140	.144	3.56	3.66	
øP1	-	.291	-	7.39	
O	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

Diagram of a 3-pin LED module with the following labels:

- TYPE
- ASSEMBLY LOCATION CODE
- DATECODE: YWW
- 4 DIGITS LOT CODE
- HALOGEN FREE: H

Rev. 2.1, 2024-12-05

Revision History

Date	Rev.	Comments
2013-09-06	2.0	Final data sheet
2024-12-05	2.1	- Update datasheet to Infineon format - Updated Part marking –page 8 - Added disclaimer on last page.

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Revision history

IRFP4127PbF

Revision 2025-01-13, Rev. 1.0

Previous revisions

Revision	Date	Subjects (major changes since last revision)
1.0	2025-01-13	Update datasheet to Infineon format, Updated Part marking –page 8

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